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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)				APPLICANT Paul R. BERGER et al		J1036 U.S. PTO 09/934334 08/21/01	
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER			DATE	NAME	CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER			DATE	COUNTRY	CLASS	SUB CLASS
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
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